



Study of anomalous effects in thermal conductivity in c-GaN/a-SiO₂ nano-composites

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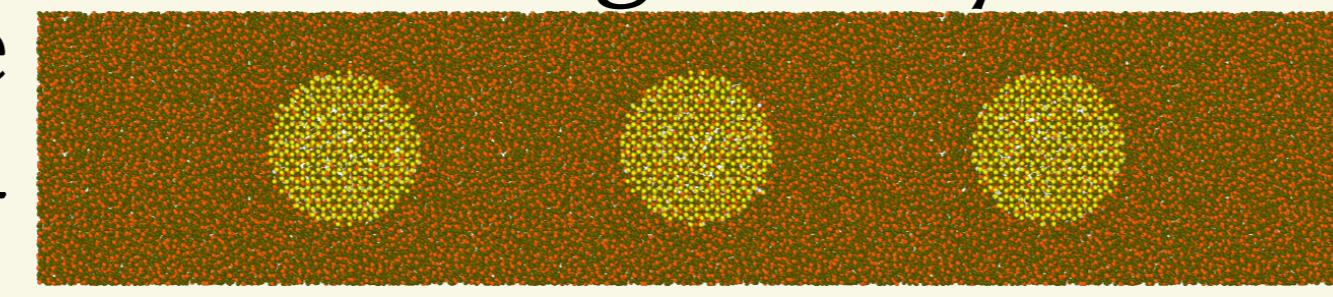
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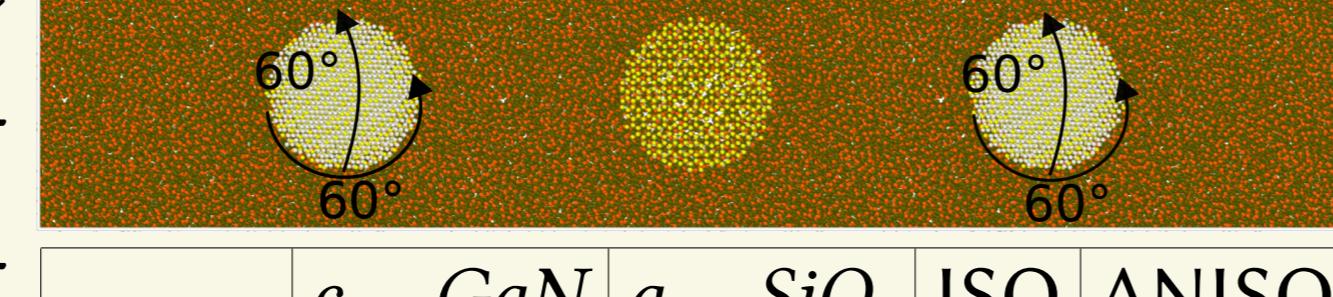
1 Introduction and Configurations

With the increasing demand of efficiency in electronic devices, a good thermal management starts to be crucial. In this regard nanocomposite can be a good solution to tune the conductivity of materials. Here we further investigate previous results [5], that shows that the thermal conductivity can depend significantly on the relative orientation of *c*-GaN inclusion in a *a*-SiO₂ matrix. Which is not taken into account in the Effective Medium Approach. We try to understand how this percolation can take place through molecular dynamics simulation.

Two configuration:
"ISO": aligned crystals



"ANISO": rotated crystals

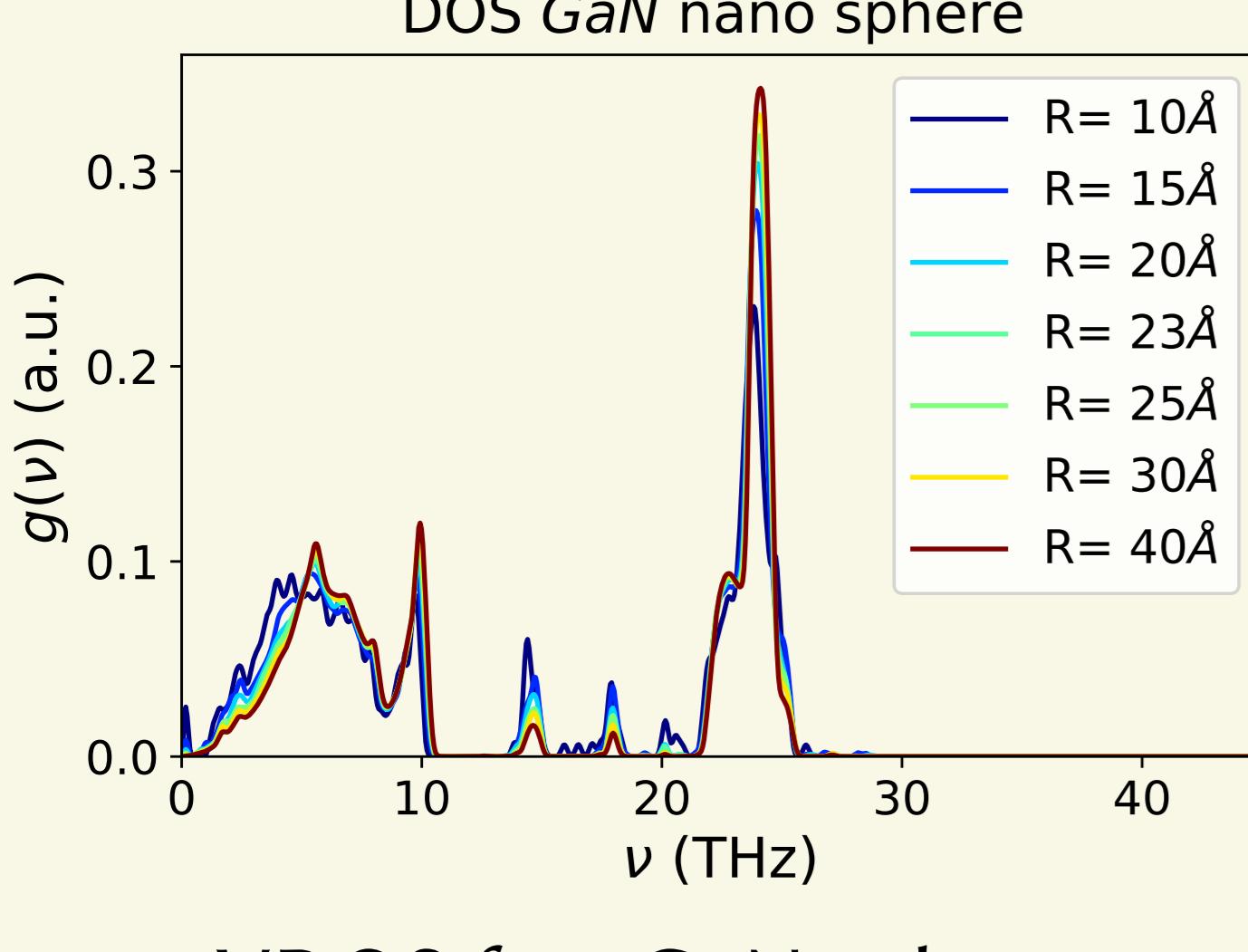


	<i>c</i> - GaN	<i>a</i> - SiO ₂	ISO	ANISO
κ W/mK	160	1.1	24.9	14.8

4 VDOS nano sphere Composites

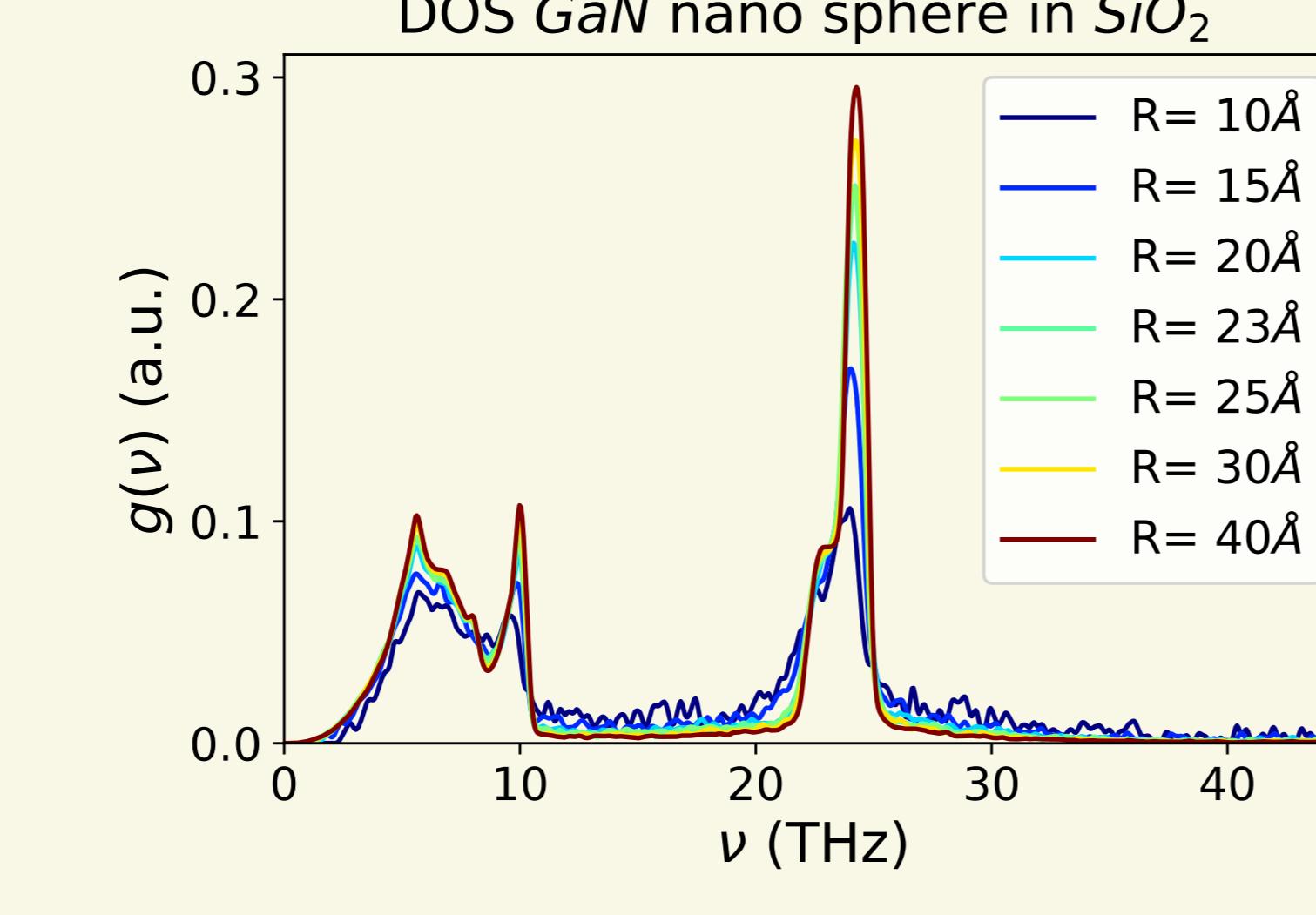
The VDOS is influenced by the size of the nano inclusion

Inclusions Size



VDOS free GaN sphere

Matrix Interface



VDOS GaN sphere in *a*-SiO₂

Red Shift of the acoustic peak

- Modes relative importance [4]

In both case with the reduction of the radius

- filling of the band gap
- reduction of the sharpness of the main peaks

Influence on the thermal conductivity

- tayloring of the EMA

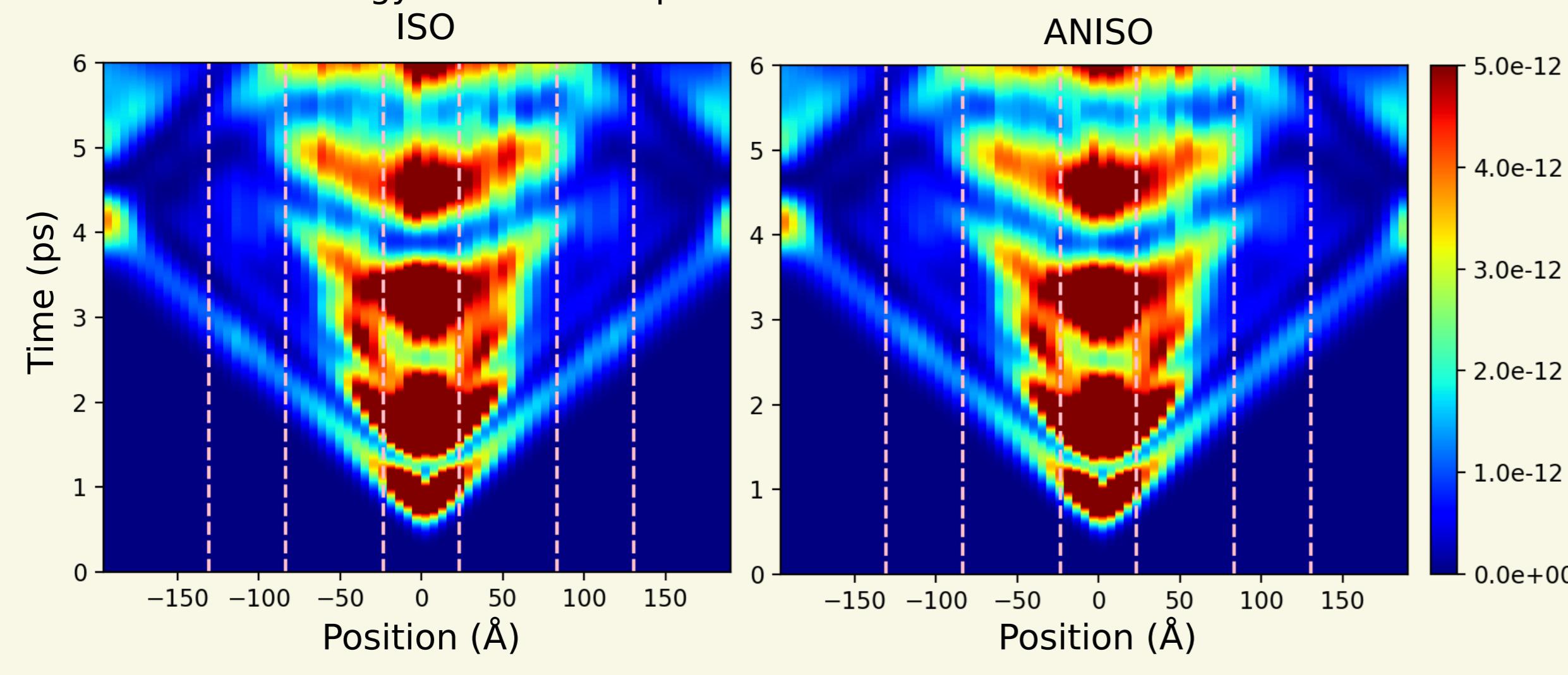
More high frequencies modes

- little to no existing studies

6 Wave packet propagation

Comparison of the propagation of an excitation from the inclusion in the middle

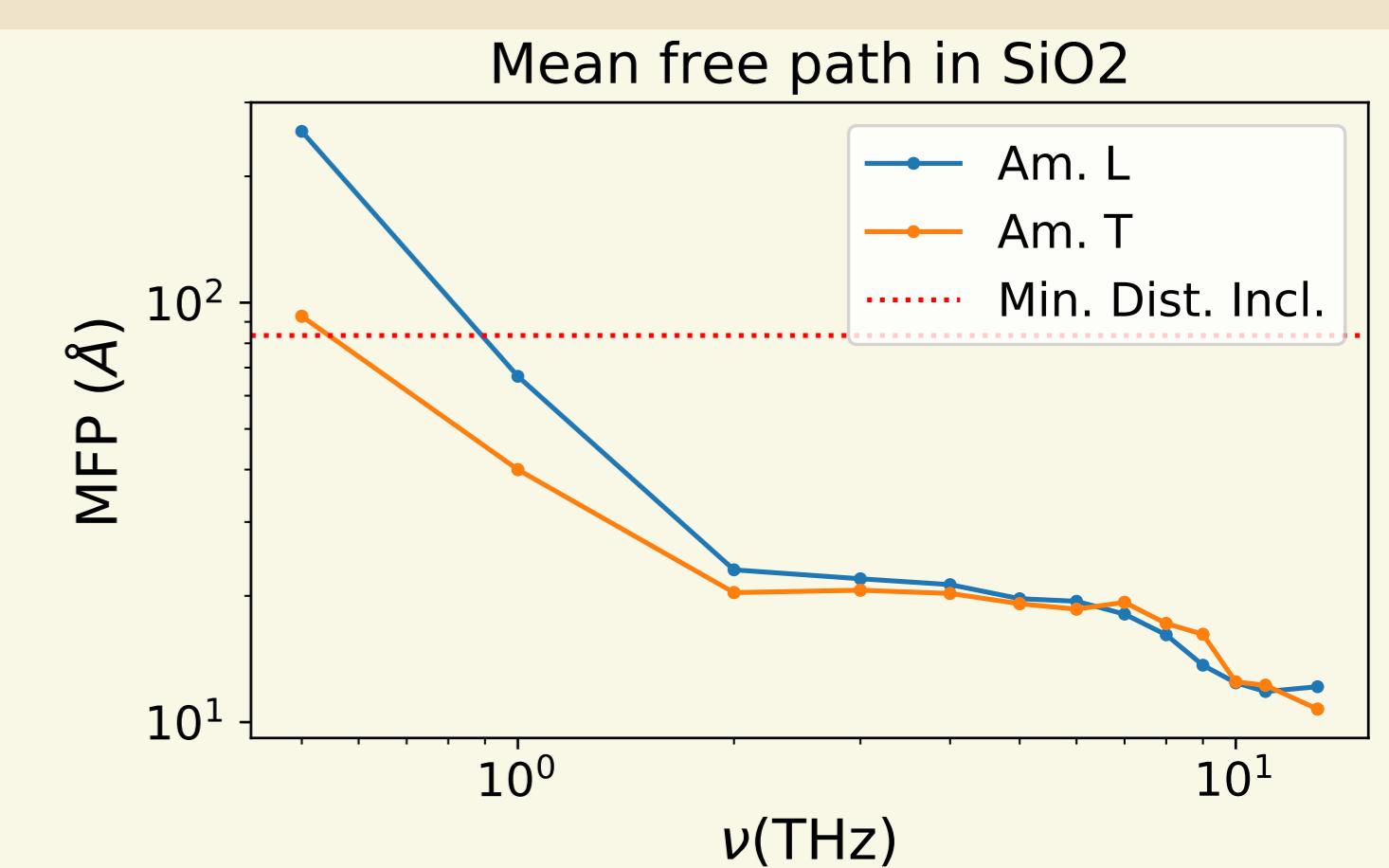
No obvious differences at 0.5 THz



2 Energie transport

Orientation dependant thermal conductivity

- Coherent wave transmission between inclusions
- Possible if Mean Free Path in SiO₂ ~ l_{incl}
- If possible at low frequency for longitudinal waves
 - Coherent with experimental results [7, 6]



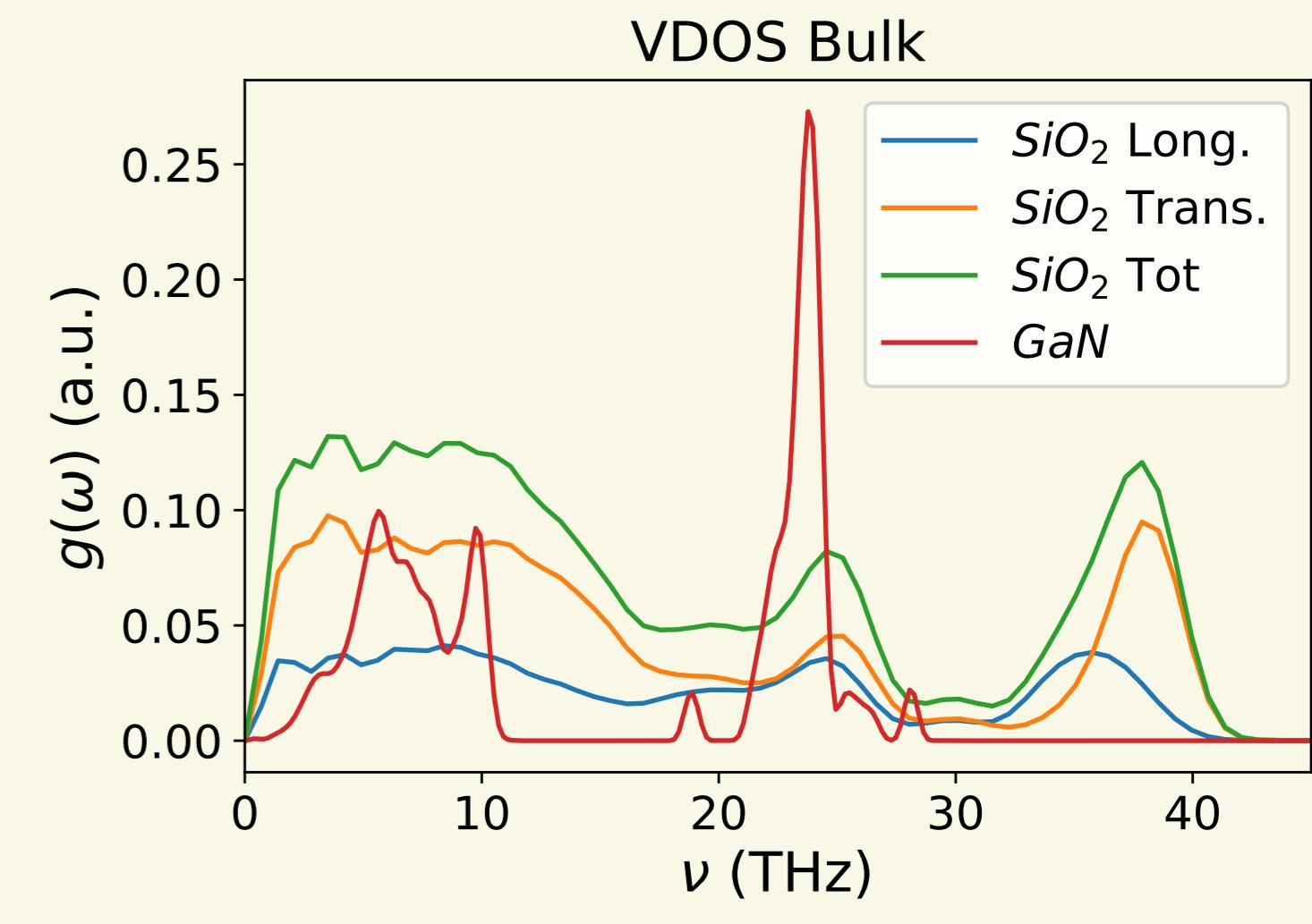
Mean Free Path in SiO₂ from wave packet attenuation [1]

3 Vibrational Density of State

To be transmitted mode of the frequency that travels should be allowed in both matrix and inclusion

Overlap between the DOS at low frequency

- in DOS of the disjunct materials



Transverse as non compressive [2]

5 Dynamical Structure Factor

We use the mode resolved dynamical structure [3]

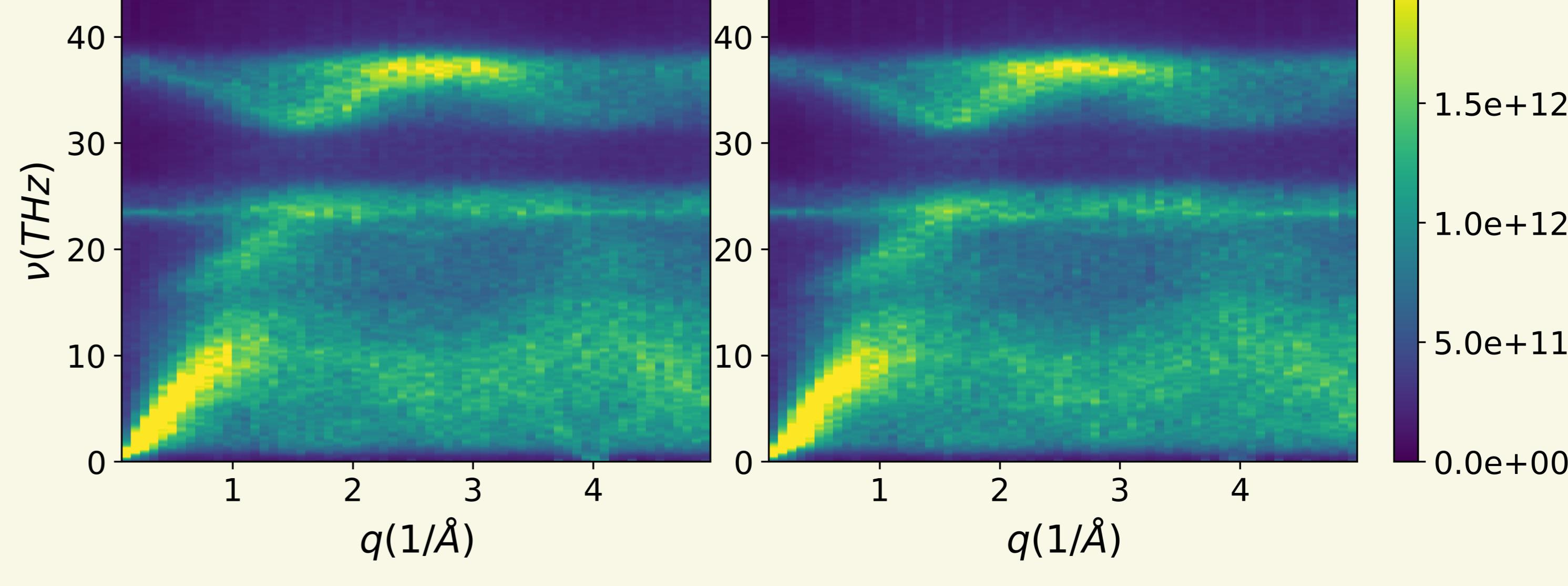
for Bulk *a*-SiO₂

- From the slope of the first phonons
- $v_L(v) > v_T(v)$

ISO/ANISO

- Apparition of a new band frequency corresponding to the GaN peak
- no obvious differences

$S(q, \nu)$ ISO (L)



Summary and prospective

Non trivial effect of size / interface to the VDOS

No obvious difference one the propagative part

- no supplementary channel in $S(q, \omega)$

Prospective

- Computation of κ via another method (NEMD)
- Test of the propagation at characteristic frequencies
 - Size of the inclusions
 - Distance between inclusion

References

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